

Subminiature Transmissive Optical Sensor with Phototransistor Output

Description

This device has a compact construction where the emitting light source and the detector is located face to face on the same optical axes. The operating wavelength is 950 nm.



Features

- Gap 2 mm
- Package height: 4 mm
- Parts shipped taped and reeled 2000 pcs/ reel
- Soldering method according to CECC00802 table 1, class B or C
- Surface Mountable Technology (SMD)
- Option X01: High rel. device advanced applications

Application

- Accurate position sensor for steering wheel
- Detection for motion direction
- Detection of motor speed and direction where high reliability performance is required

Pin Connection

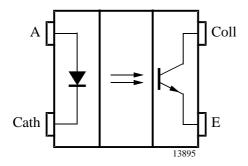


Figure 1.

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TCPT1200X01



Absolute Maximum Ratings

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Reverse voltage		V _R	5	V
Forward current		I_{F}	25	mA
Pulse forward current	$t_p = 0.1 \text{ ms}; t_{p/T} = 0.01$	I _{FP}	100	mA
Power dissipation	$T_{amb} \le 25^{\circ}C$	P _v	75	mW

Output (Detector)

Parameters	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V _{CE0}	70	V
Emitter collector voltage		V _{EC0}	7	V
Collector current		I _C	20	mA
Power dissipation	$T_{amb} \le 25^{\circ}C$	P _v	75	mW

Coupler

Parameters	Test Conditions	Symbol	Value	Unit
Total power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	150	mW
Ambient temperature range		T _{amb}	-40 to + 85	°C
Storage temperature range		T _{stg}	-40 to + 100	°C
Soldering temperature	t ≤ 5 s	T _{sd}	230	°C

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Electrical Characteristics

 $T_{amb} = 25^{\circ}C$

Input (Emitter)

Parameters	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 15 \text{ mA}$	V_{F}		1.2	1.5	V
Reverse current	$V_R = 5 \text{ V}$	I_R			10	μΑ
Junction capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C _j		50		pF

Output (Detector)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector emitter voltage	$I_C = 1 \text{ mA}$	V_{CE0}	70			V
Emitter collector voltage	$I_E = 100 \mu A$	V _{EC0}	7			V
Collector emitter cut-off current	$V_{CE} = 25 \text{ V}, I_F = 0,$ E = 0	I _{CE0}		10	100	nA

Coupler

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector current	$V_{CE} = 5 \text{ V, IF} = 15 \text{ mA}$	I_{C}	300	500		μΑ
Collector/emitter saturation voltage	$I_F = 15 \text{ mA},$ $I_C = 0.05 \text{ mA}$	V _{CEsat}			0.4	V

Derating Diagram

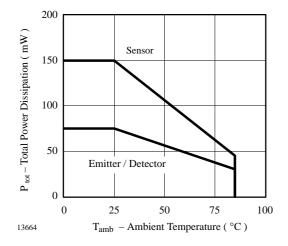


Figure 2.

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Application Example

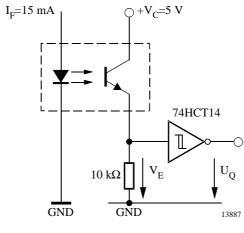
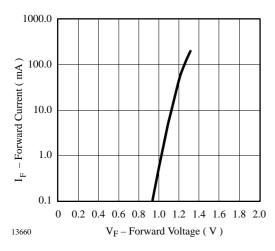
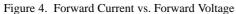


Figure 3.

Typical Characteristics ($T_{amb} = 25$ °C, unless otherwise specified)





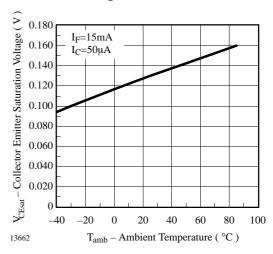


Figure 5. Collector Em. Sat. Voltage vs. Ambient Temperature

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Typical Characteristics ($T_{amb} = 25$ °C, unless otherwise specified)

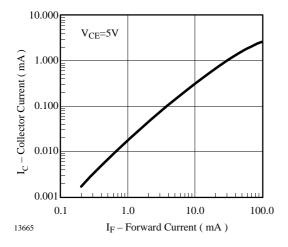


Figure 6. Collector Current vs. Forward Current

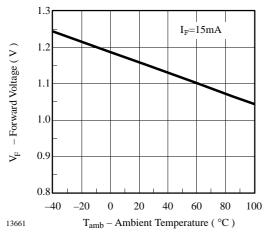


Figure 7. Forward Voltage vs. Ambient Temperature

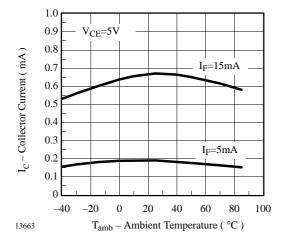


Figure 8. Collector Current vs. Ambient Temperature

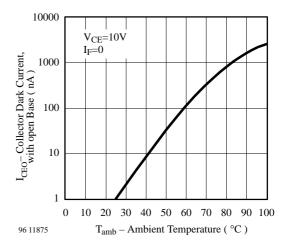


Figure 9. Collector Dark Current vs. Ambient Temperature

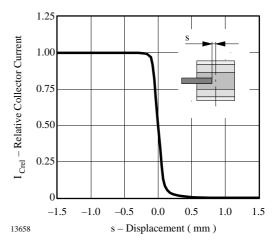
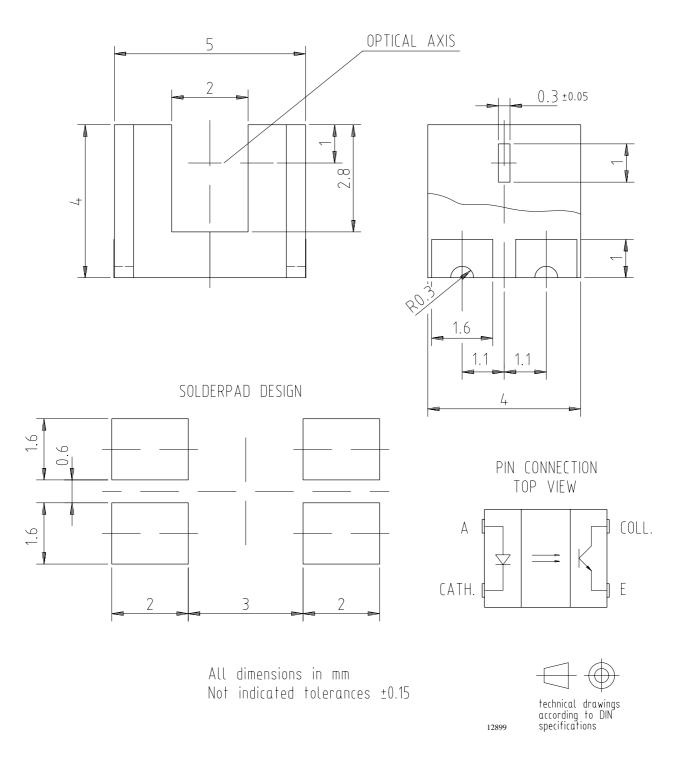


Figure 10. Rel. Collector Current vs. Distance

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Dimensions in mm

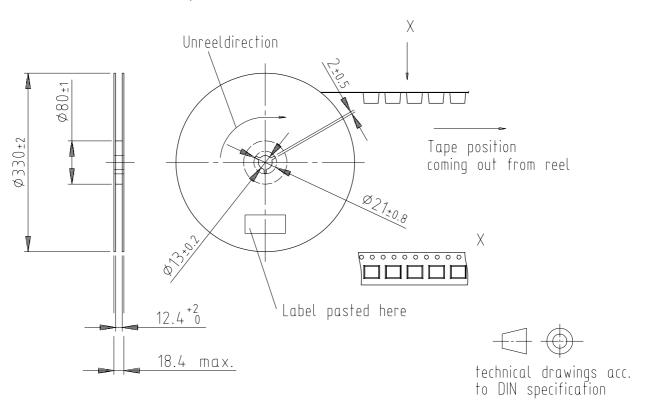


weight: ca. 0.15 g

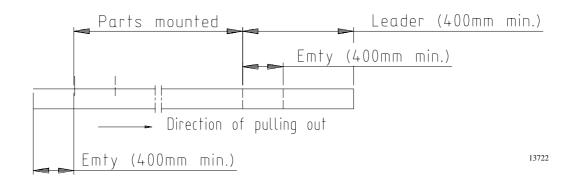


Reel Dimensions

Reel-dimension and shape:



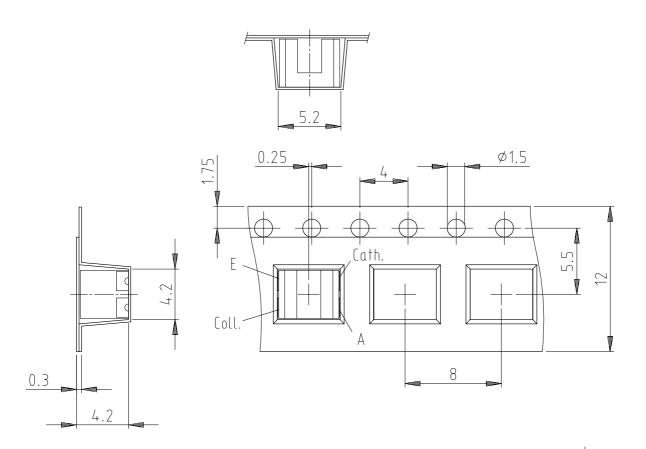
Leader and trailer tape:



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Tape Dimensions



Quantity per reel: 2000 pcs.

technical drawings acc. to DIN specification

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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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